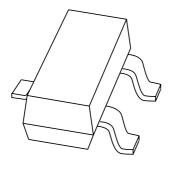
## **DISCRETE SEMICONDUCTORS**

## DATA SHEET



# **BAT721 series**Schottky barrier (double) diodes

Product specification Supersedes data of 1999 May 06 2001 Oct 12





## Schottky barrier (double) diodes

## **BAT721** series

#### **FEATURES**

- · Ultra high switching speed
- · Low forward voltage
- · Guard ring protected
- Small plastic SMD package.

#### **APPLICATIONS**

- Ultra high-speed switching
- Voltage clamping
- Protection circuits.

## **DESCRIPTION**

Planar Schottky barrier diodes encapsulated in a SOT23 small plastic SMD package. Single diodes and double diodes with different pinning are available.

## **MARKING**

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BAT721	L7*
BAT721A	L8*
BAT721C	L9*
BAT721S	L0*

#### Note

- 1. \* = p : Made in Hong Kong.\* = t : Made in Malaysia.
  - \* = W: Made in China.

#### PINNING

PIN	BAT721				
FIN		Α	С	S	
1	а	k <sub>1</sub>	a <sub>1</sub>	a <sub>1</sub>	
2	n.c.	k <sub>2</sub>	a <sub>2</sub>	k <sub>2</sub>	
3	k	a <sub>1</sub> , a <sub>2</sub>	k <sub>1</sub> , k <sub>2</sub>	k <sub>1</sub> , a <sub>2</sub>	

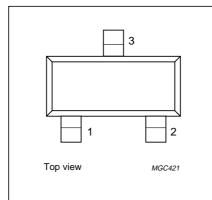


Fig.1 Simplified outline (SOT23) and pin configuration.

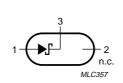


Fig.2 BAT721 single diode configuration (symbol).

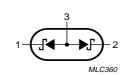


Fig.3 BAT721A diode configuration (symbol).

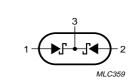


Fig.4 BAT721C diode configuration (symbol).

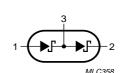


Fig.5 BAT721S diode configuration (symbol).

## Schottky barrier (double) diodes

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## **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_R$	continuous reverse voltage		_	40	V
I <sub>F</sub>	continuous forward current		_	200	mA
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 8.3 ms half sinewave; JEDEC method	_	1	A
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C

## **ELECTRICAL CHARACTERISTICS**

 $T_i = 25$  °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>F</sub>	continuous forward voltage	see Fig.6			
		I <sub>F</sub> = 10 mA	_	300	mV
		I <sub>F</sub> = 100 mA	_	420	mV
		I <sub>F</sub> = 200 mA	_	550	mV
I <sub>R</sub>	continuous reverse current	V <sub>R</sub> = 30 V; see Fig.7	_	15	μΑ
		$V_R = 30 \text{ V}; T_j = 100 ^{\circ}\text{C}; \text{ see Fig.7}$	_	3	mA
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0; see Fig.8	40	50	pF

## Note

1. Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	note 1	500	K/W

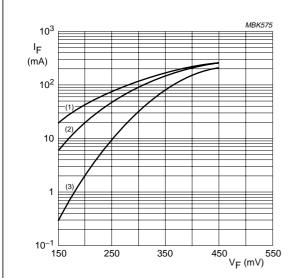
## Note

1. Refer to SOT23 standard mounting conditions.

## Schottky barrier (double) diodes

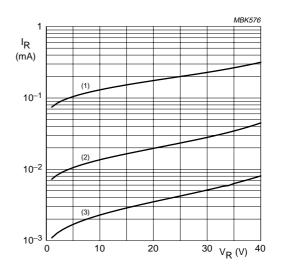
## BAT721 series

## **GRAPHICAL DATA**



- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.6 Forward current as a function of forward voltage; typical values.



- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.7 Reverse current as a function of reverse voltage; typical values.

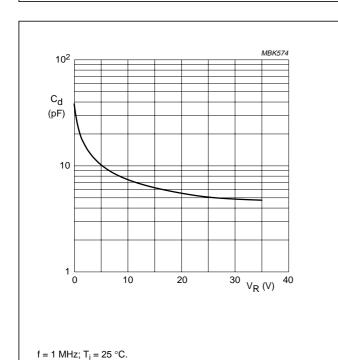


Fig.8 Diode capacitance as a function of reverse voltage; typical values.

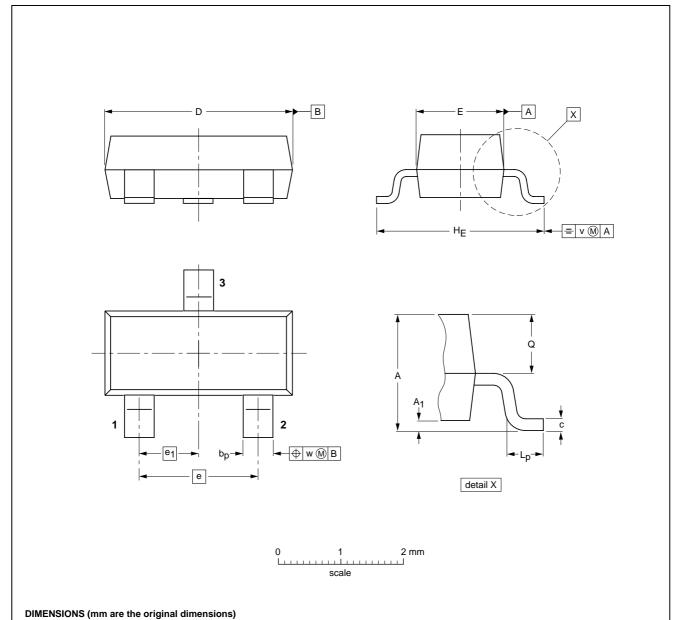
## Schottky barrier (double) diodes

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## **PACKAGE OUTLINE**

Plastic surface mounted package; 3 leads

SOT23



OUTLINE		REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT23		TO-236AB				<del>97-02-28</del> 99-09-13	

 $L_{p}$ 

0.45

 $H_{\mathsf{E}}$ 

Q

0.55

w

0.1

Ε

1.9

2001 Oct 12 5

 $\mathbf{A}_{\mathbf{1}}$ 

max.

0.48

0.15

1.1

UNIT

## Schottky barrier (double) diodes

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#### **DATA SHEET STATUS**

DATA SHEET STATUS(1)	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
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## Schottky barrier (double) diodes

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NOTES

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